

TITLE PAGE

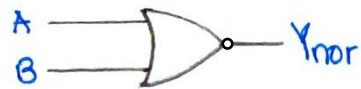
| | | |
|---------------------|---|-----------------------------|
| Class | : | BE - 8 |
| Roll. No | : | 42428 |
| Assignment No. | : | B. 1d , 1e |
| Assignment Name | : | 2 input CMOS NOR & OR Gates |
| Date Of Performance | : | 12-11-2020 |

Theory:

$$F = 90 \text{ nm}$$

Symbols-

2 i/p NOR Gate



$$Y_{\text{nor}} = \overline{A+B}$$

2 i/p OR Gate.



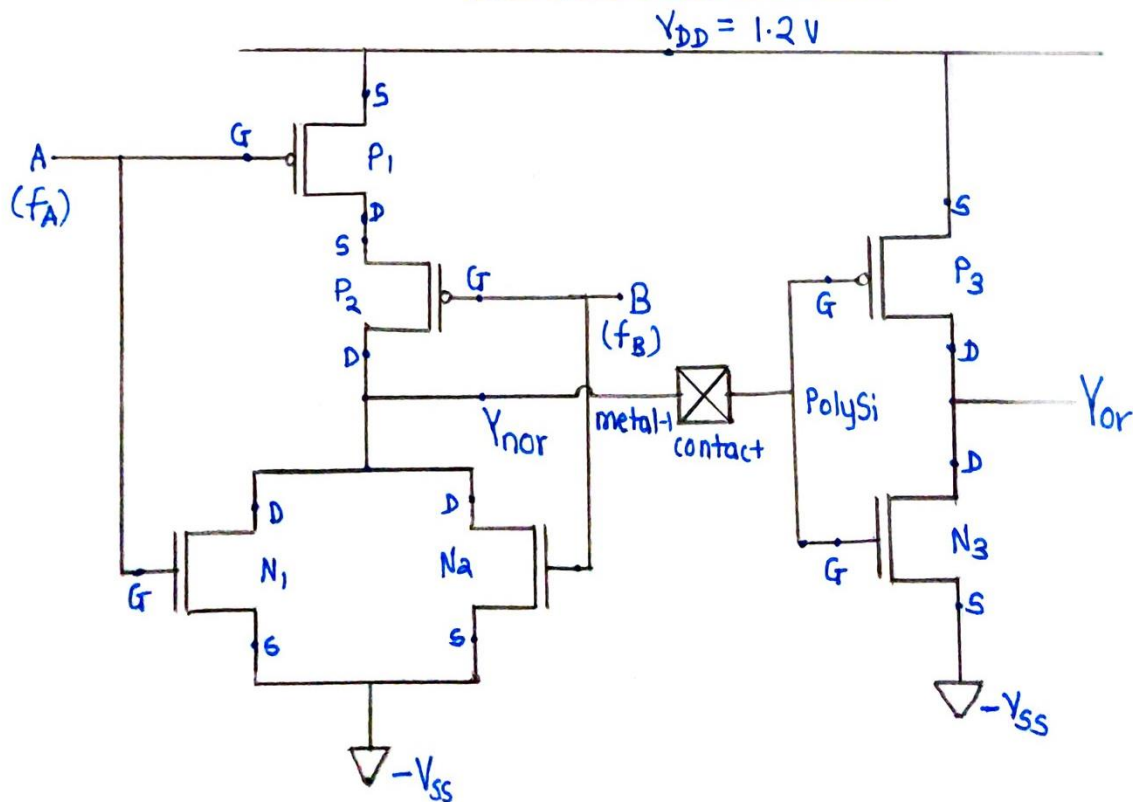
$$Y_{\text{or}} = A+B$$

Truth Tables

| A | B | Y_{nor} |
|---|---|------------------|
| 0 | 0 | 1 |
| 0 | 1 | 0 |
| 1 | 0 | 0 |
| 1 | 1 | 0 |

| A | B | Y_{or} |
|---|---|-----------------|
| 0 | 0 | 0 |
| 0 | 1 | 1 |
| 1 | 0 | 1 |
| 1 | 1 | 1 |

Combined Schematic



$$f_B = 2f_A$$

Size of each PMOS Transistor (P_1, P_2, P_3)

$$P = \left(\frac{500}{100} \right) \text{nm} = 5$$

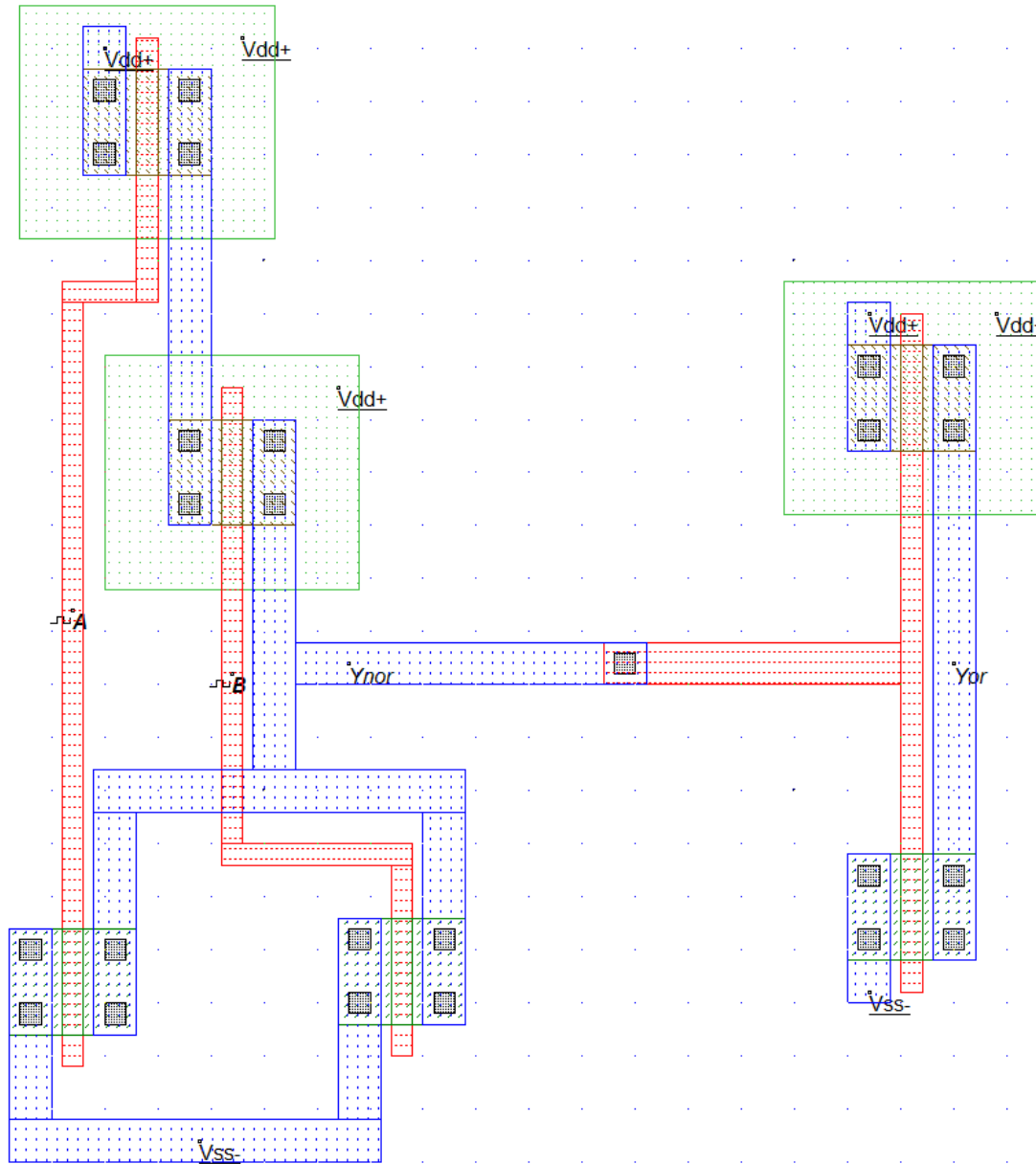
Size of each NMOS Transistor (N_1, N_2, N_3)

$$n = \left(\frac{500}{100} \right) \text{nm} = 5$$

$$\text{Relative Size} = \frac{P}{n} = 1$$

LAYOUT

5 lambda
0.250um



Palette

Options

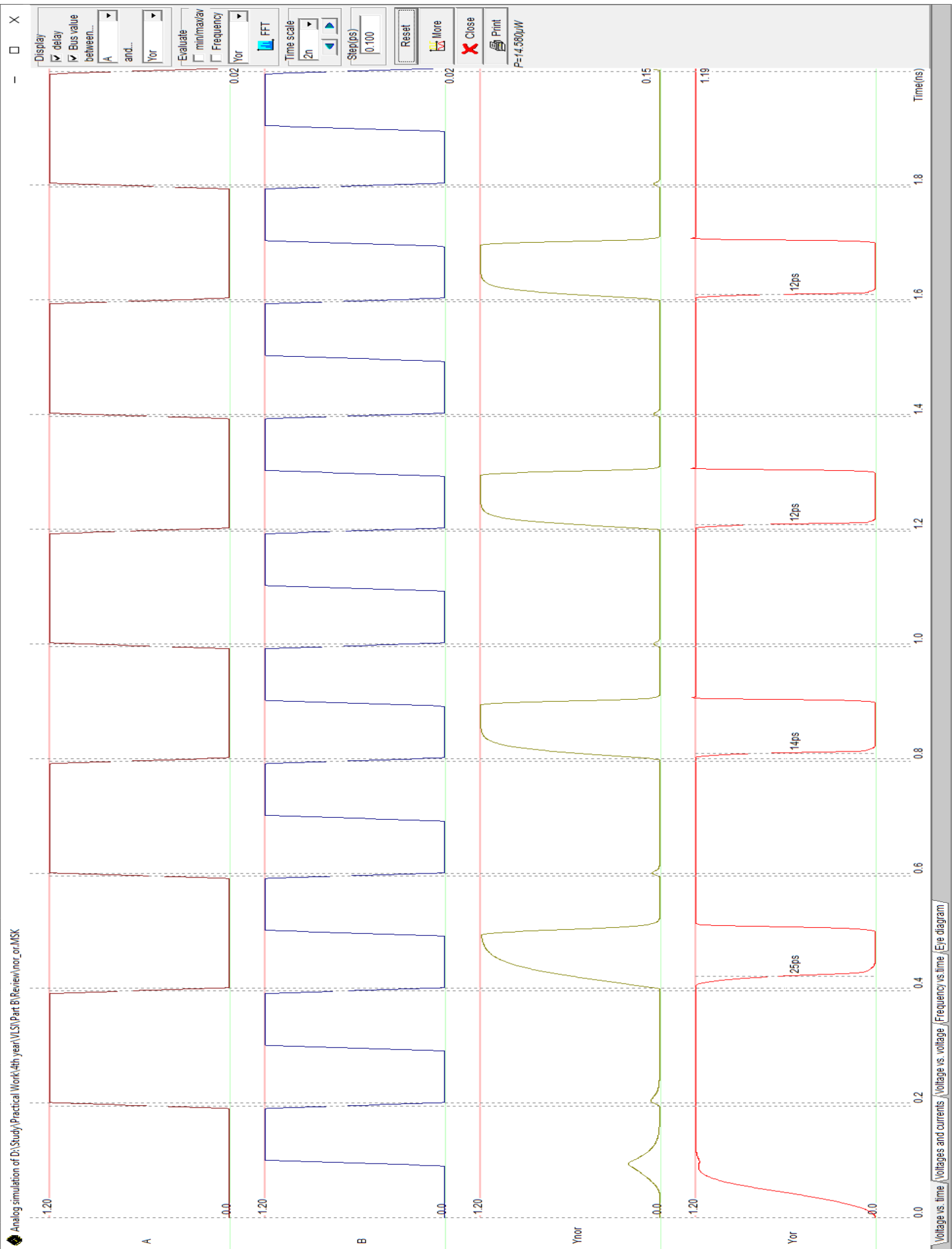
| | |
|---------------|--|
| Metal 6 | |
| Metal 5 | |
| Metal 4 | |
| Metal 3 | |
| Metal 2 | |
| Metal 1 | |
| Polysilicon 2 | |
| Contact | |
| Polysilicon | |
| P+ Diffusion | |
| N+ Diffusion | |
| N Well | |

Show palette menu...

Yand

CMOS 90nm, 6 Metal Copper - strained SiGe - LowK (1.20V,2.50V)

Waveforms



Conclusion:

Thus we have :

- 1) Drawn the LAYOUT for CMOS NOR & OR Gates using 90 nm Foundry.
- 2) Simulated the LAYOUT to observe waveforms & verified its functionality as per TRUTH-TABLE.